## Product Quality Information

# nexperia

## Quality Information for Product Type PTVS8V0P1UP

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### Quick reference

| Information                  | Content        |
|------------------------------|----------------|
| Device Type                  | PTVS8V0P1UP    |
| Ordering Information (12NCs) | 9340 641 57115 |
| Qualification Grade          | automotive     |
| Package                      | SOD128 (CFP5)  |
| Waferfab                     | Nexperia DHAM  |
| Assembly                     | Nexperia ATSN  |
| ESD HBM                      | > 8000 V       |
| Calculated Failure Rate      | 0.52 FIT       |
| MTBF/MTTF                    | 1.92E+09 hours |

### **Explanation**

Automotive qualified products are in accordance with the AEC-Q101.

Electrostatic Discharge (ESD) tests are performed as described in the AEC-Q101 with each 3 positive and 3 negative pulses for each stress voltage level.

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, AEC-Q101 Test # 5). The parameters for calculation of FIT and MTBF/MTTF are as follows: Confidence level 60%, junction temperature derated to 55 °C, activation energy 0.7 eV, test time 168 - 1000 hrs.

For discrete semiconductor devices the Mean Time Between Failure (MTBF) is replaced by the Mean Time To Failure (MTTF) acronym. MTTF is calculated from the Intrinsic Failure Rate.

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